

Symbol	Tr1:Nch	Tr2:Pch
$V_{DSS}$	30V	-30V
$R_{DS(on)}(Max.)$	16.0m $\Omega$	28.6m $\Omega$
$I_D$	$\pm 9.0A$	$\pm 8.0A$
$P_D$	2.6W	

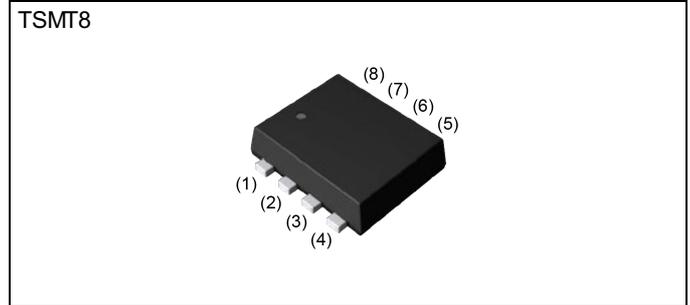
### ●Features

- 1) Low on - resistance.
- 2) Small Surface Mount Package (TSMT8).
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

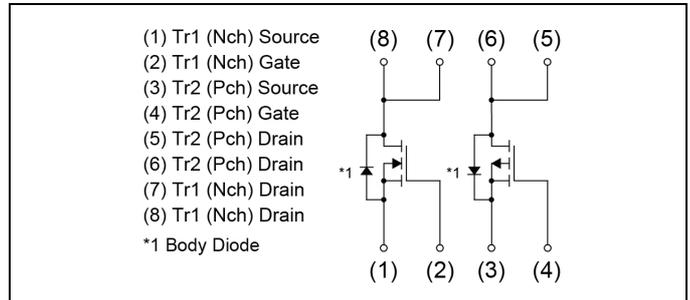
### ●Application

Switching

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	MA4

### ●Absolute maximum ratings ( $T_a = 25^\circ C$ ), unless otherwise specified.

Parameter	Symbol	Value		Unit
		Tr1:Nch	Tr2:Pch	
Drain - Source voltage	$V_{DSS}$	30	-30	V
Continuous drain current	$I_D^{*1}$	$\pm 9.0$	$\pm 8.0$	A
Pulsed drain current	$I_{D,pulse}^{*2}$	$\pm 18$	$\pm 18$	A
Gate - Source voltage	$V_{GSS}$	$\pm 20$	$\pm 20$	V
Avalanche energy, single pulse	$E_{AS}^{*4}$	3.5	2.2	mJ
Avalanche current	$I_{AS}^{*4}$	7.0	-5.5	A
Power dissipation	total	$P_D^{*1}$	2.6	W
		$P_D^{*3}$	1.5	
	element	$P_D^{*3}$	1.25	
Junction temperature	$T_j$	150	$^\circ C$	
Range of storage temperature	$T_{stg}$	-55 to +150	$^\circ C$	

### ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*3}$	-	-	83.3	°C/W

### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ ) , unless otherwise specified

Parameter	Symbol	Type	Conditions	Values			Unit
				Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	Tr1	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
		Tr2	$V_{GS} = 0V, I_D = -1mA$	-30	-	-	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	Tr1	$I_D = 1mA$ , referenced to $25^\circ\text{C}$	-	21	-	mV/°C
		Tr2	$I_D = -1mA$ , referenced to $25^\circ\text{C}$	-	-22	-	
Zero gate voltage drain current	$I_{DSS}$	Tr1	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
		Tr2	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	
Gate - Source leakage current	$I_{GSS}$	Tr1	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±100	nA
		Tr2	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±100	
Gate threshold voltage	$V_{GS(th)}$	Tr1	$V_{DS} = V_{GS}, I_D = 1mA$	1.0	-	2.5	V
		Tr2	$V_{DS} = V_{GS}, I_D = -1mA$	-1.0	-	-2.5	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	Tr1	$I_D = 1mA$ , referenced to $25^\circ\text{C}$	-	-3	-	mV/°C
		Tr2	$I_D = -1mA$ , referenced to $25^\circ\text{C}$	-	2.9	-	
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	Tr1	$V_{GS} = 10V, I_D = 9A$	-	12.3	16.0	mΩ
			$V_{GS} = 4.5V, I_D = 7A$	-	18.2	23.7	
		Tr2	$V_{GS} = -10V, I_D = -8A$	-	22.0	28.6	
			$V_{GS} = -4.5V, I_D = -5.5A$	-	31.0	40.3	
Gate input resistance	$R_G$	Tr1	$f=1MHz$ , open drain	-	3.3	-	Ω
		Tr2		-	6.0	-	
Transconductance	$g_{fs}^{*5}$	Tr1	$V_{DS} = 5V, I_D = 7A$	4.4	-	-	S
		Tr2	$V_{DS} = -5V, I_D = -5.5A$	5.5	-	-	

\*1  $P_w \leq 1s$ , Limited only by maximum temperature allowed.

\*2  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

\*3 Mounted on a ceramic board (30×30×0.8mm)

\*4 Tr1:  $L \approx 0.1mH$ ,  $V_{DD} = 15V$ ,  $R_G = 25\Omega$ , STARTING  $T_j = 25^\circ\text{C}$  Fig.3-1,3-2

Tr2:  $L \approx 0.1mH$ ,  $V_{DD} = -15V$ ,  $R_G = 25\Omega$ , STARTING  $T_j = 25^\circ\text{C}$  Fig.6-1,6-2

\*5 Pulsed

● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

<Tr1>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	640	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = 15V$	-	110	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	90	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 15V, V_{GS} = 10V$	-	8	-	ns
Rise time	$t_r^{*5}$	$I_D = 4.5A$	-	19	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 3.3\Omega$	-	33	-	
Fall time	$t_f^{*5}$	$R_G = 10\Omega$	-	7	-	

<Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	890	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = -15V$	-	160	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	125	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx -15V, V_{GS} = -10V$	-	10	-	ns
Rise time	$t_r^{*5}$	$I_D = -4A$	-	16	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 3.8\Omega$	-	55	-	
Fall time	$t_f^{*5}$	$R_G = 10\Omega$	-	22	-	

● Gate charge characteristics ( $T_a = 25^\circ\text{C}$ )

<Tr1>

Parameter	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
Total gate charge	$Q_g^{*5}$	$V_{DD} \approx 15\text{V}$ $I_D = 9\text{A}$	$V_{GS} = 10\text{V}$	-	15.5	-	nC
Gate - Source charge	$Q_{gs}^{*5}$		$V_{GS} = 4.5\text{V}$	-	7.9	-	
Gate - Drain charge	$Q_{gd}^{*5}$			-	2.8	-	

<Tr2>

Parameter	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
Total gate charge	$Q_g^{*5}$	$V_{DD} \approx -15\text{V}$ $I_D = -8\text{A}$	$V_{GS} = -10\text{V}$	-	19.6	-	nC
Gate - Source charge	$Q_{gs}^{*5}$		$V_{GS} = -4.5\text{V}$	-	9.8	-	
Gate - Drain charge	$Q_{gd}^{*5}$			-	3.0	-	

● Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

<Tr1>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	$I_S$	$T_a = 25^\circ\text{C}$	-	-	1.0	A
Body diode pulse current	$I_{SP}^{*2}$		-	-	18	
Forward voltage	$V_{SD}^{*5}$	$V_{GS} = 0\text{V}, I_S = 1\text{A}$	-	-	1.2	V

<Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	$I_S$	$T_a = 25^\circ\text{C}$	-	-	-1.0	A
Body diode pulse current	$I_{SP}^{*2}$		-	-	-18	
Forward voltage	$V_{SD}^{*5}$	$V_{GS} = 0\text{V}, I_S = -1\text{A}$	-	-	-1.2	V

●Electrical characteristic curves <Tr1>

Fig.1 Power Dissipation Derating Curve

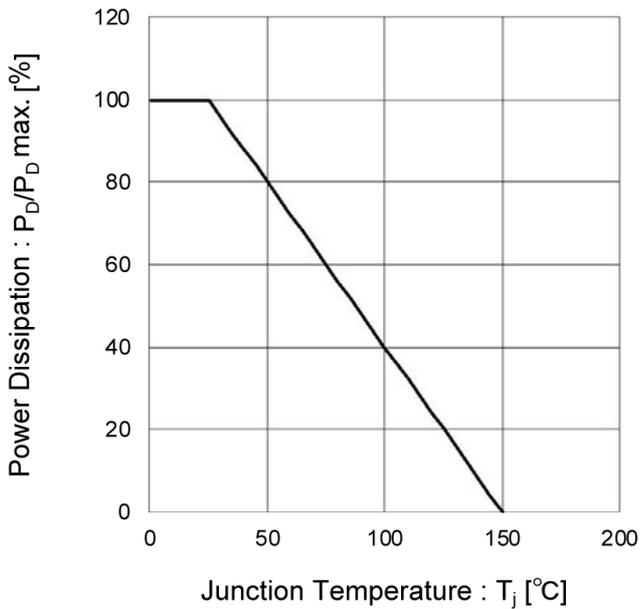


Fig.2 Maximum Safe Operating Area

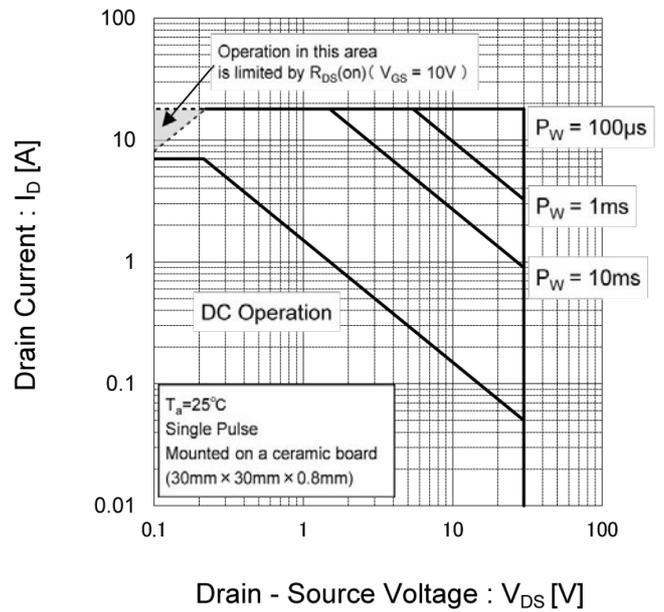


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

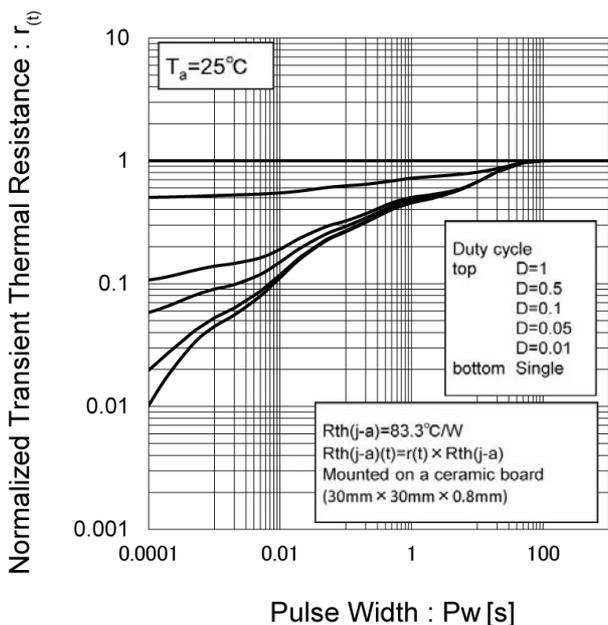
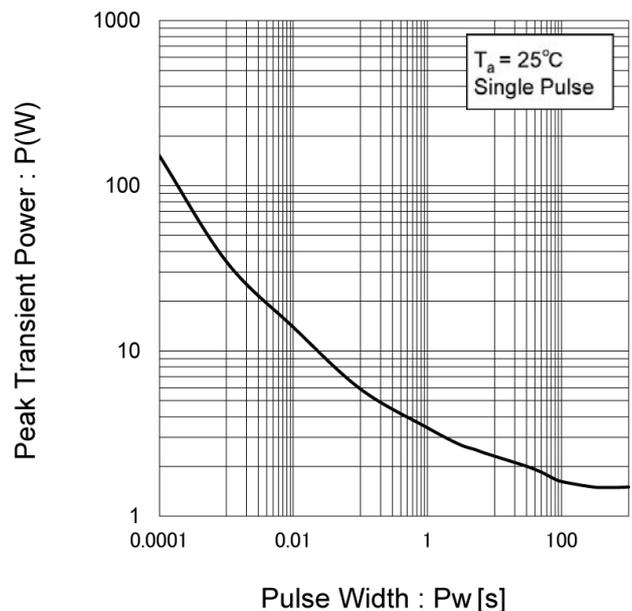


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves <Tr1>

Fig.5 Typical Output Characteristics(I)

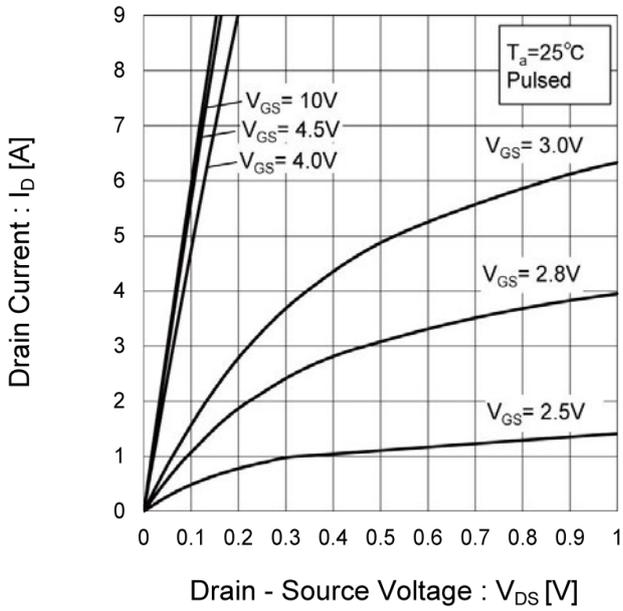


Fig.6 Typical Output Characteristics(II)

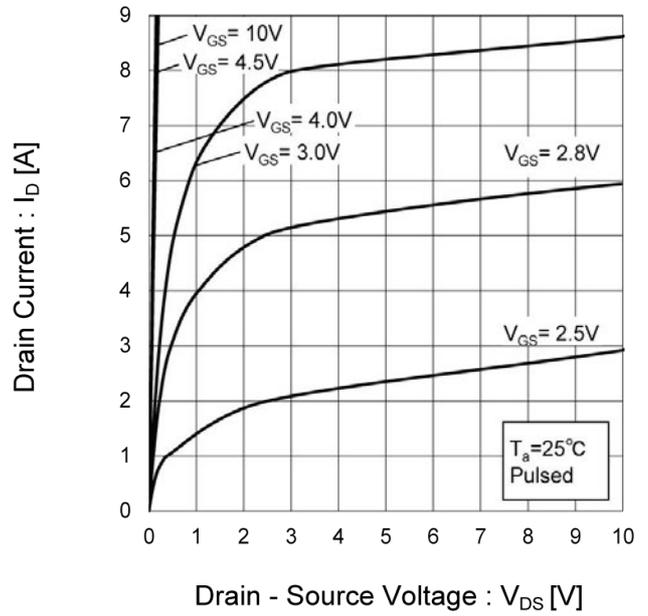
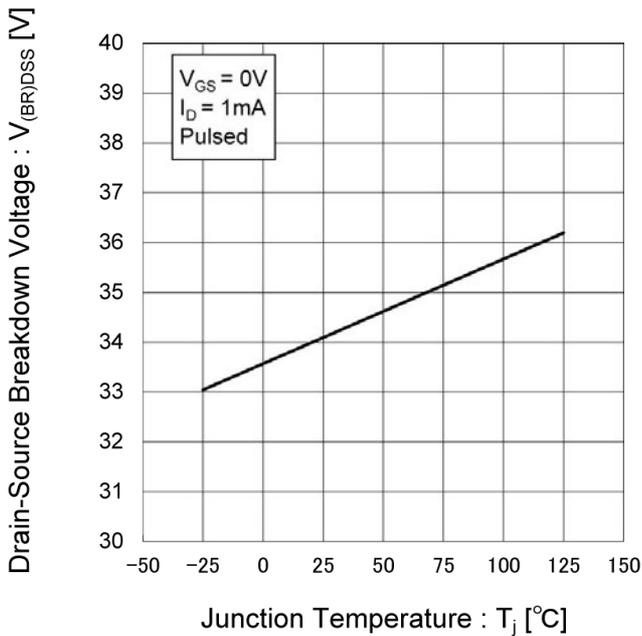


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves <Tr1>

Fig.8 Typical Transfer Characteristics

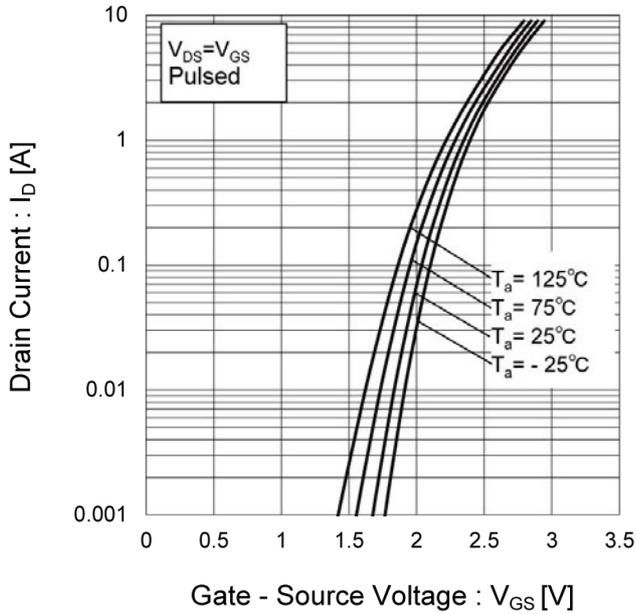


Fig.9 Gate Threshold Voltage vs. Junction Temperature

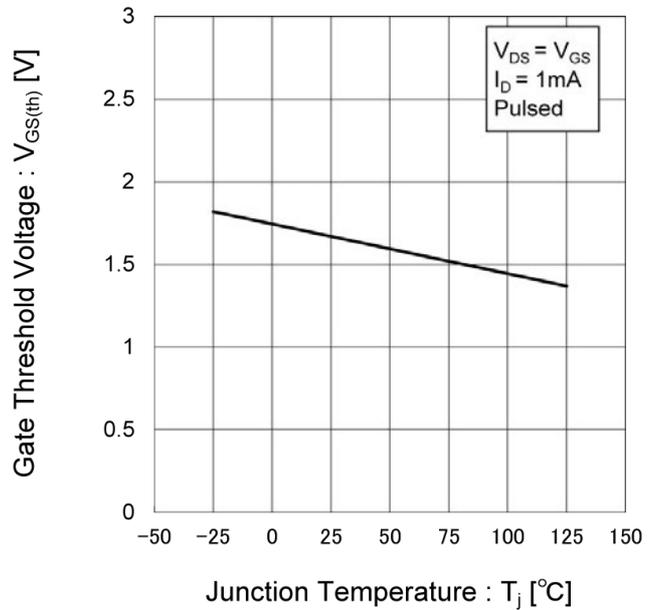
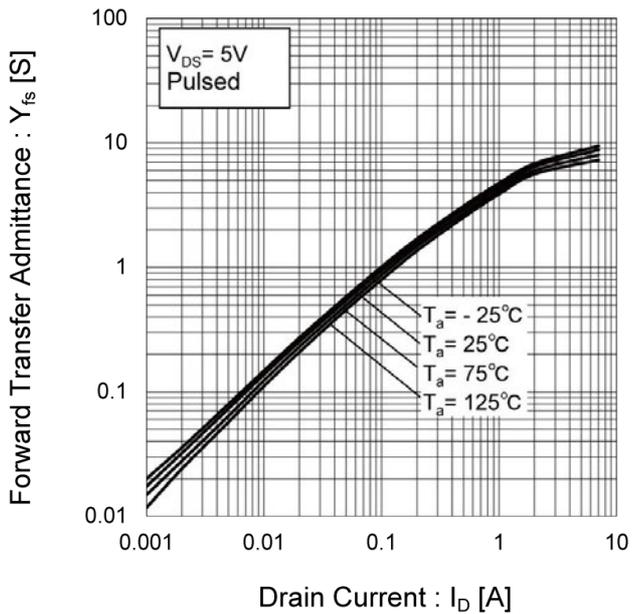


Fig.10 Transconductance vs. Drain Current



●Electrical characteristic curves <Tr1>

Fig.11 Drain Current Derating Curve

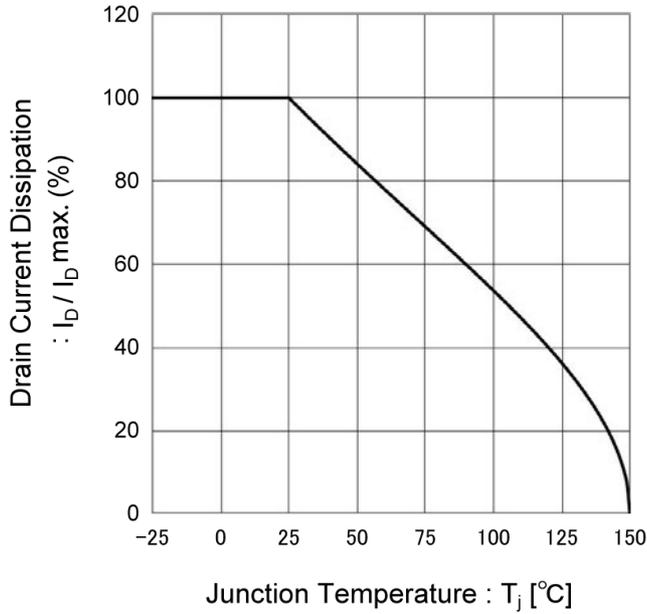


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

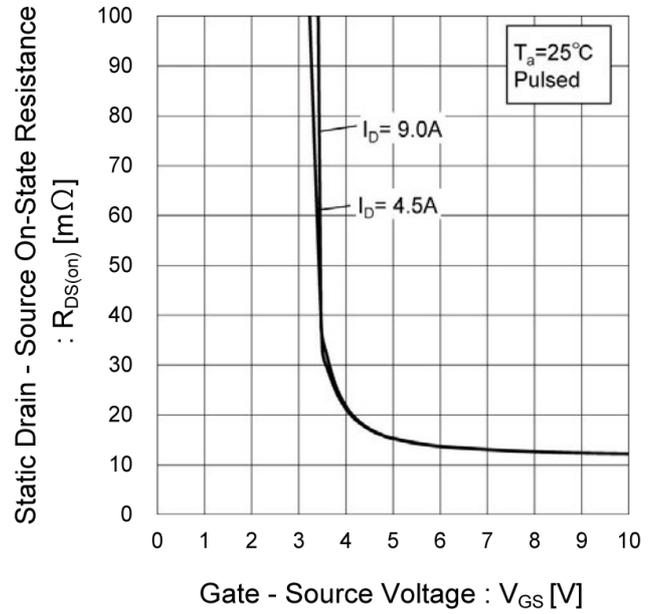
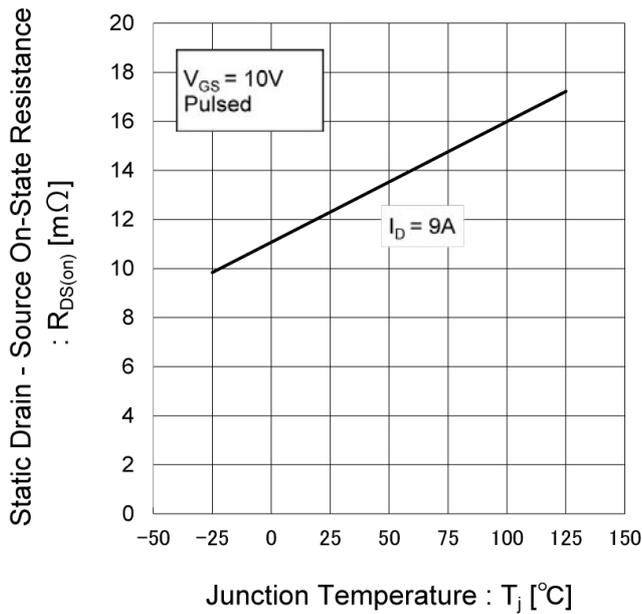


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves <Tr1>

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

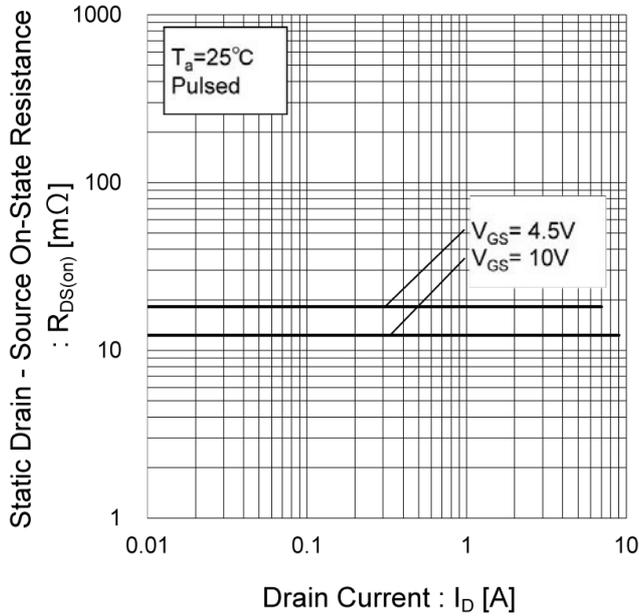


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

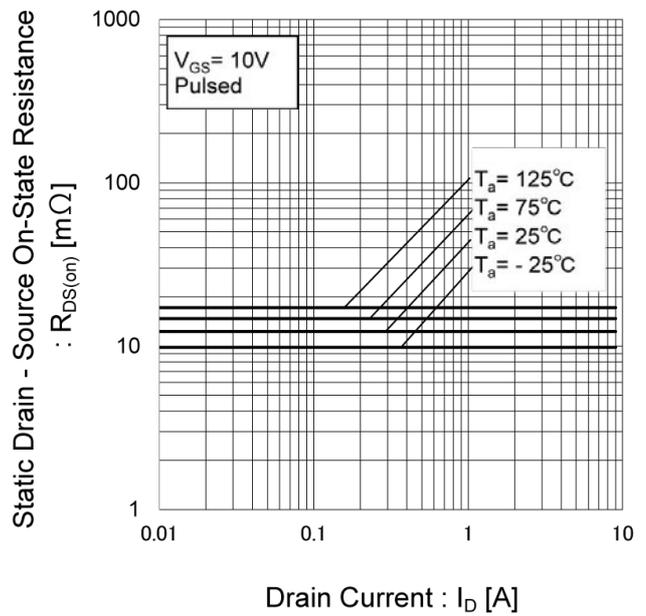
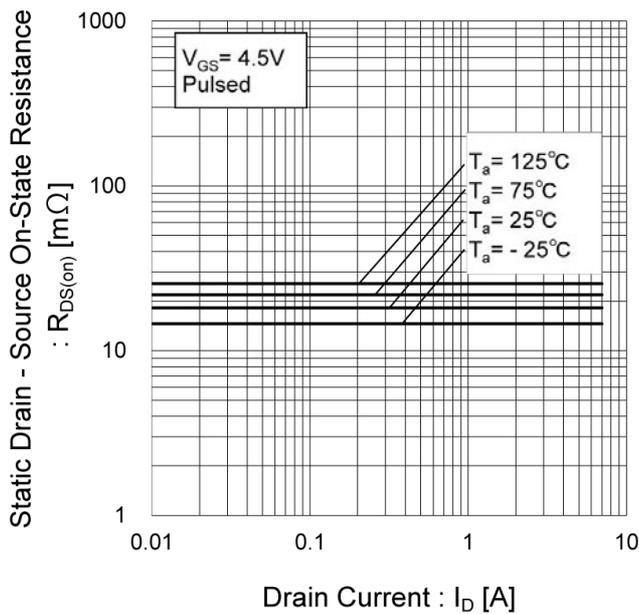


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



●Electrical characteristic curves <Tr1>

Fig.17 Typical Capacitance vs. Drain - Source Voltage

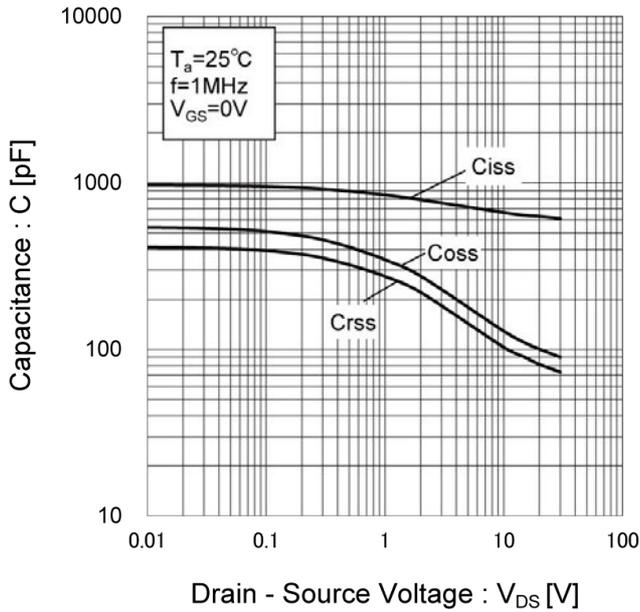


Fig.18 Switching Characteristics

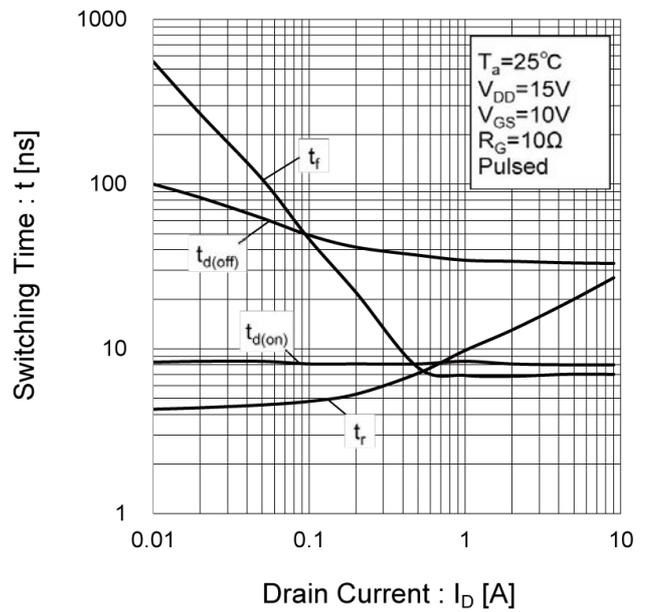


Fig.19 Dynamic Input Characteristics

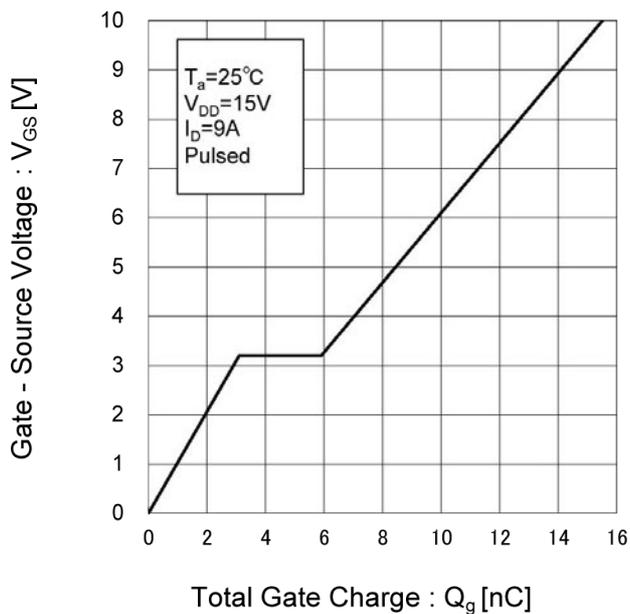
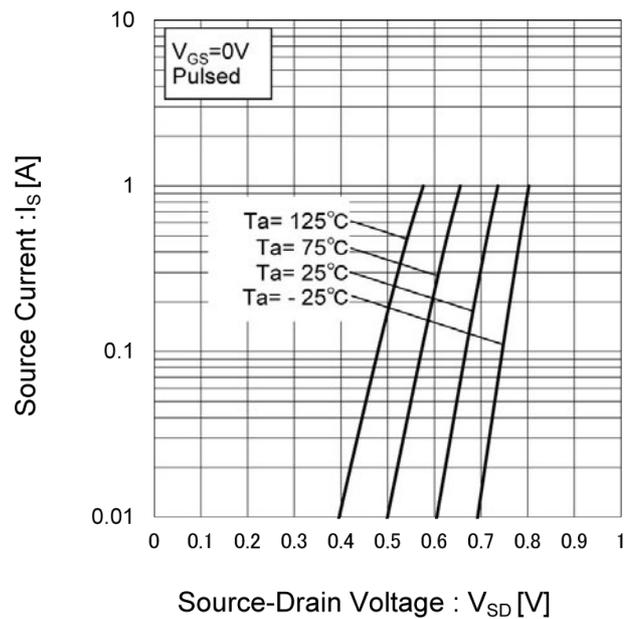


Fig.20 Source Current vs. Source Drain Voltage



● Electrical characteristic curves <Tr2>

Fig.1 Power Dissipation Derating Curve

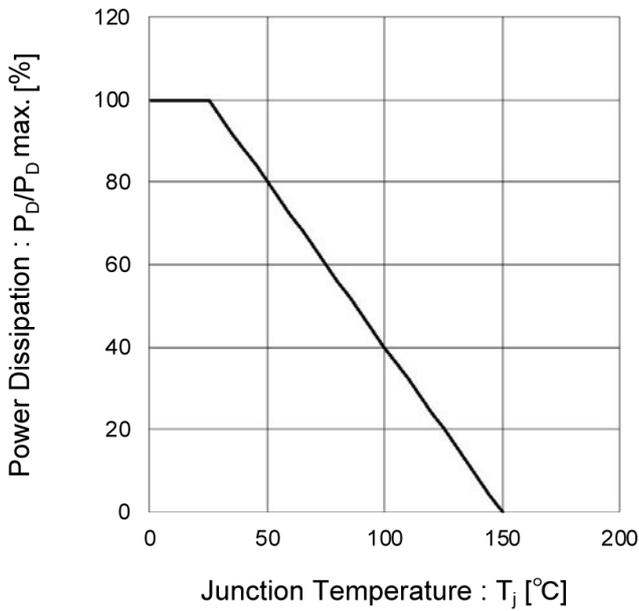


Fig.2 Maximum Safe Operating Area

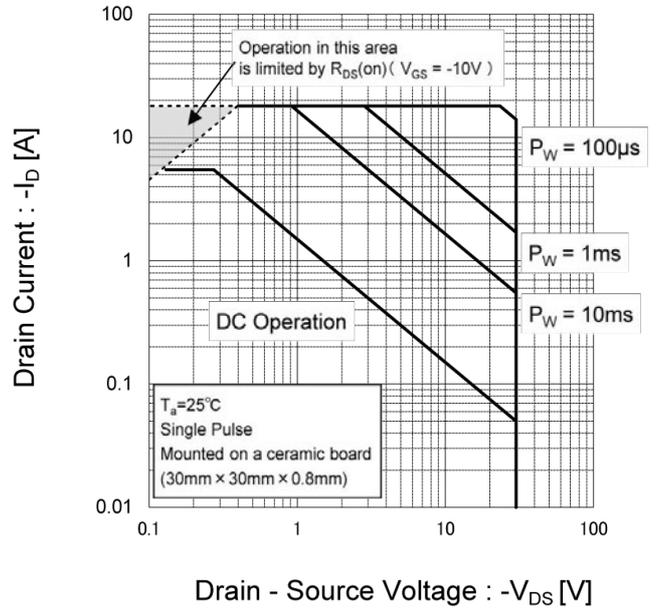


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

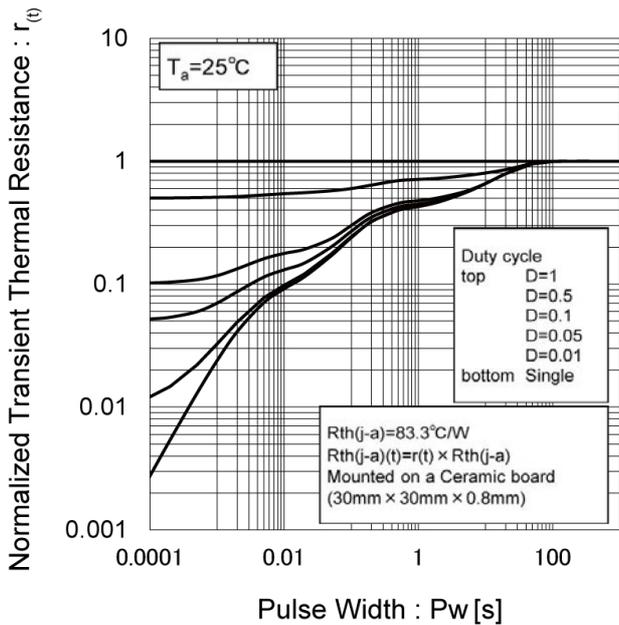
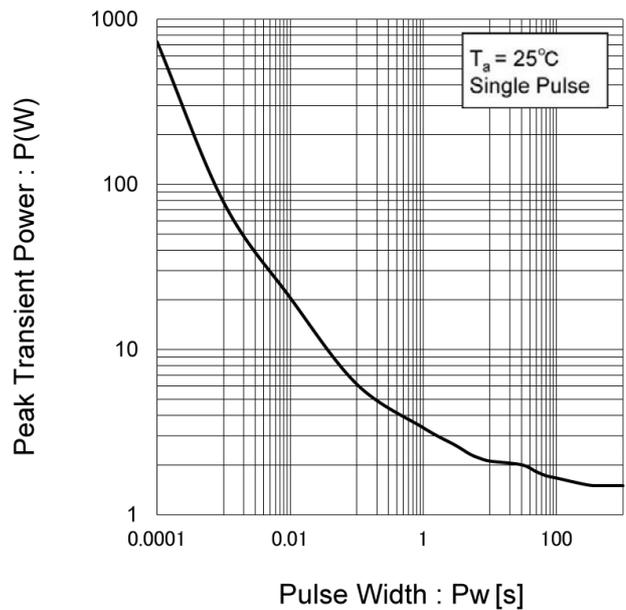


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves <Tr2>

Fig.5 Typical Output Characteristics(I)

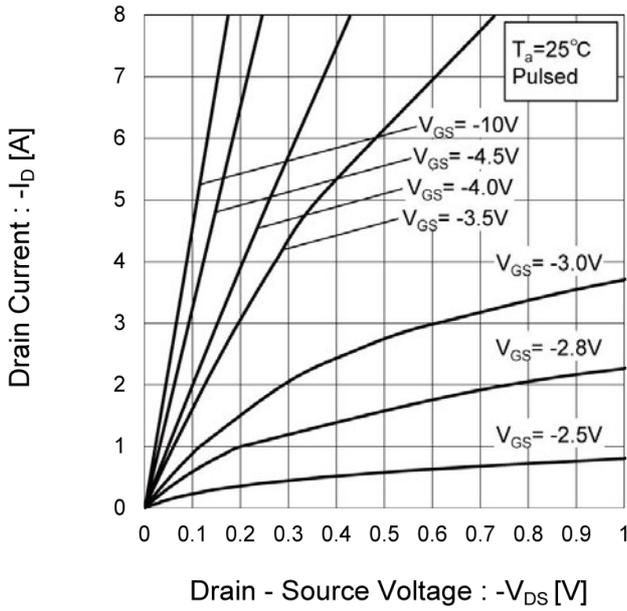


Fig.6 Typical Output Characteristics(II)

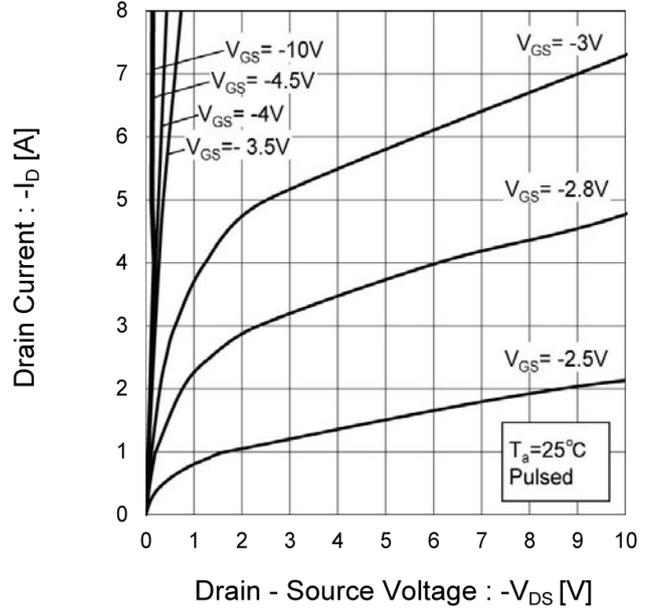
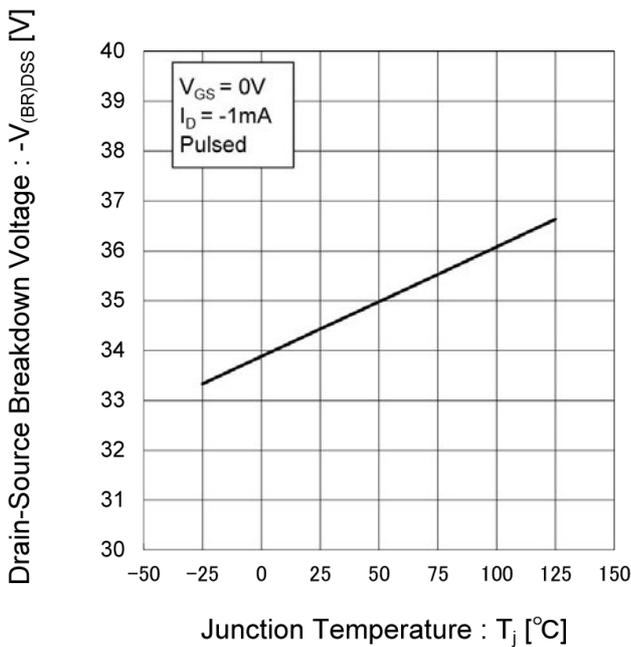


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves <Tr2>

Fig.8 Typical Transfer Characteristics

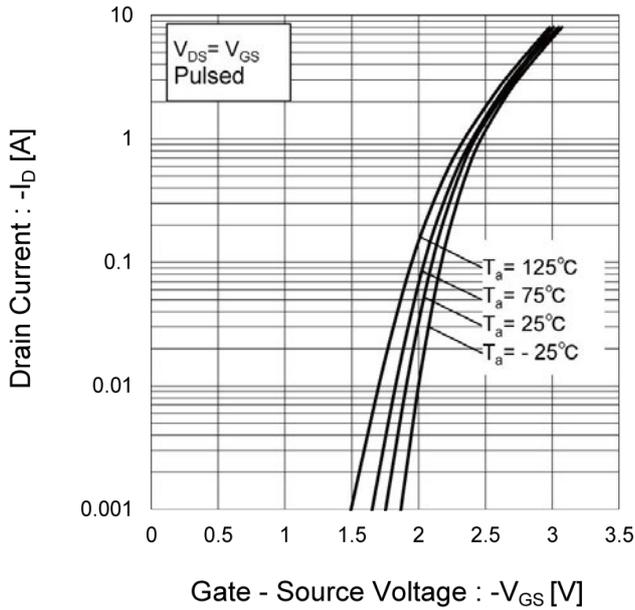


Fig.9 Gate Threshold Voltage vs. Junction Temperature

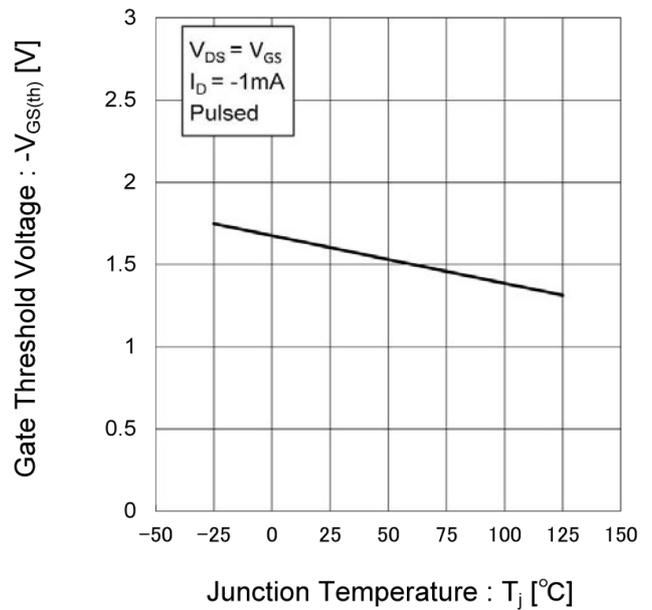
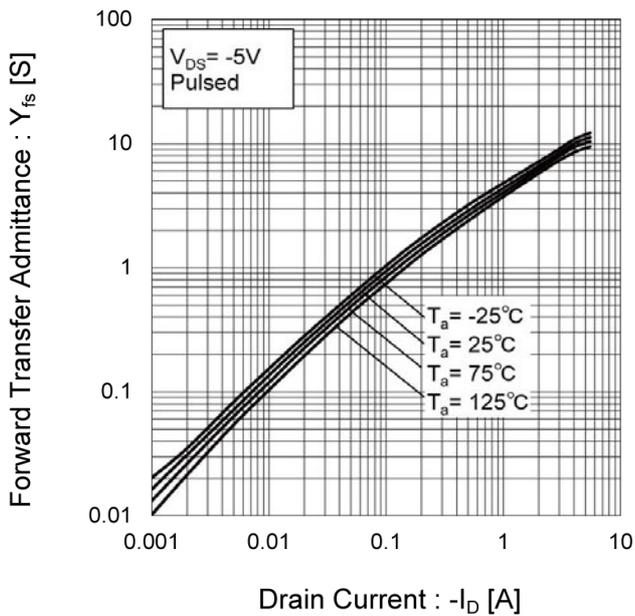


Fig.10 Transconductance vs. Drain Current



●Electrical characteristic curves <Tr2>

Fig.11 Drain Current Derating Curve

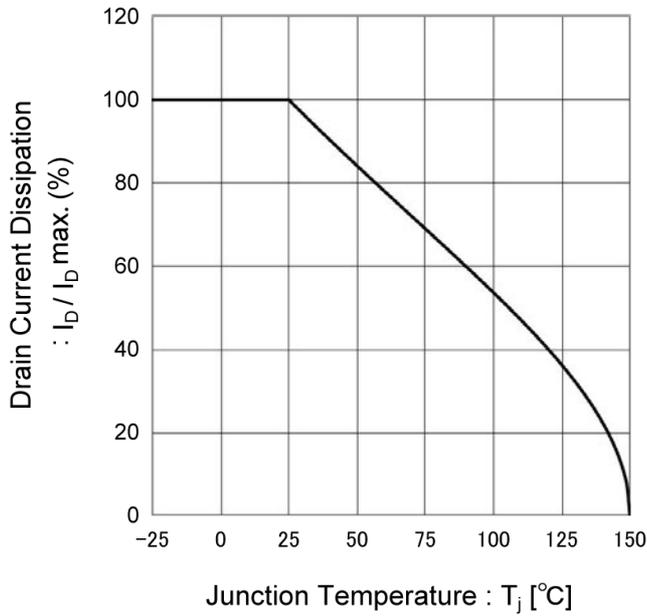


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

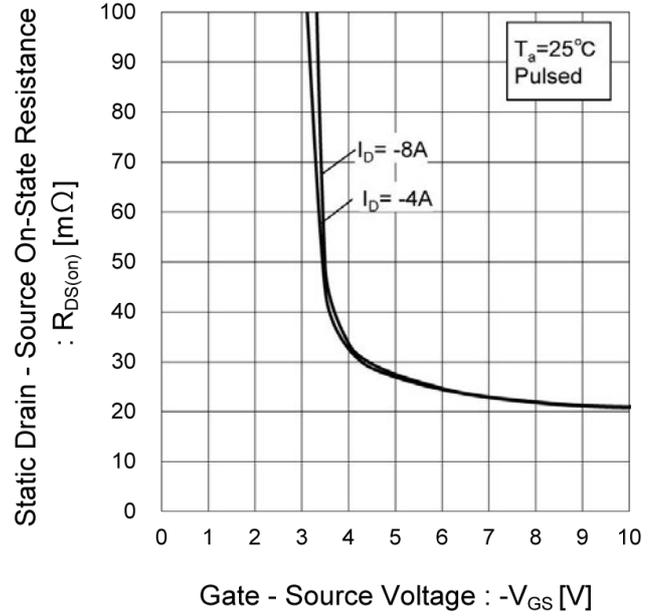
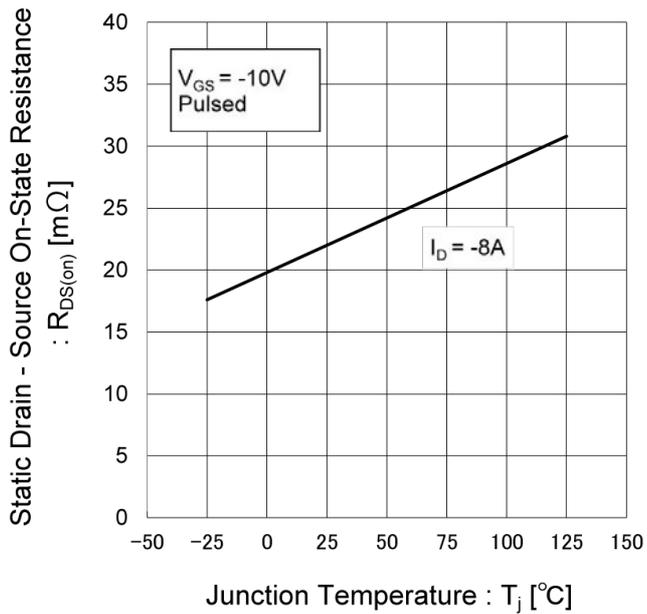


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves <Tr2>

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

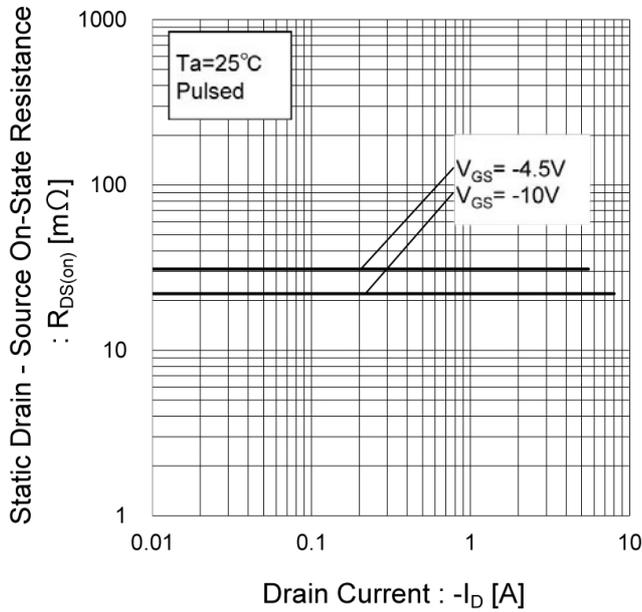


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

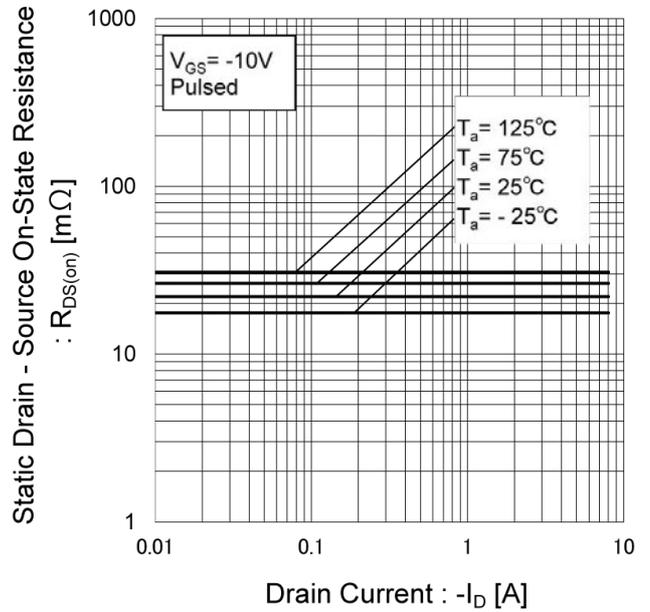
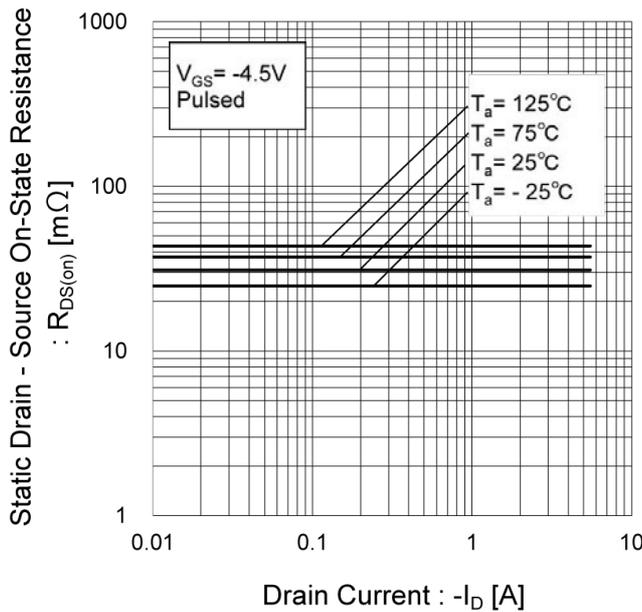


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



●Electrical characteristic curves <Tr2>

Fig.17 Typical Capacitance vs. Drain - Source Voltage

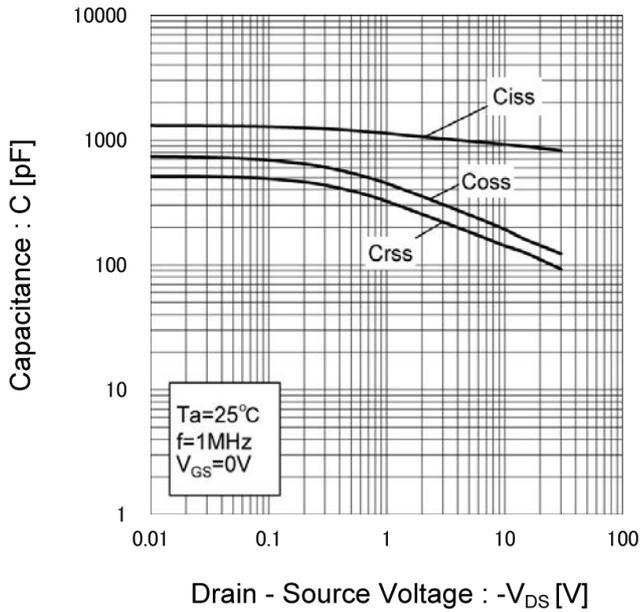


Fig.18 Switching Characteristics

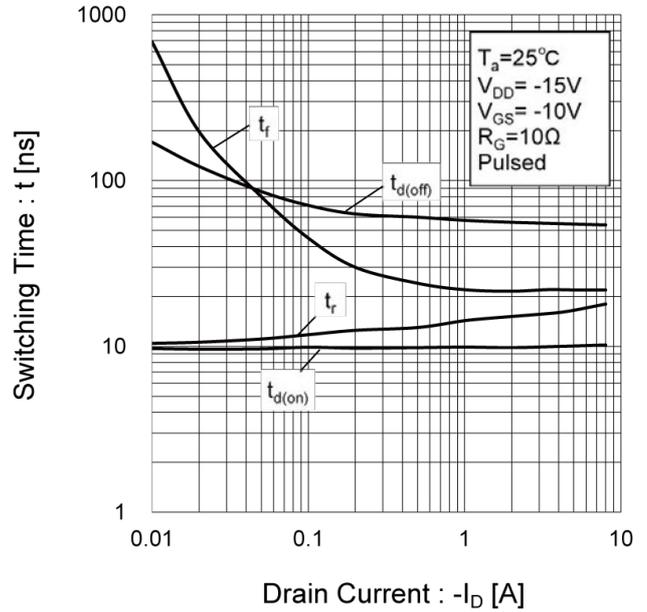


Fig.19 Dynamic Input Characteristics

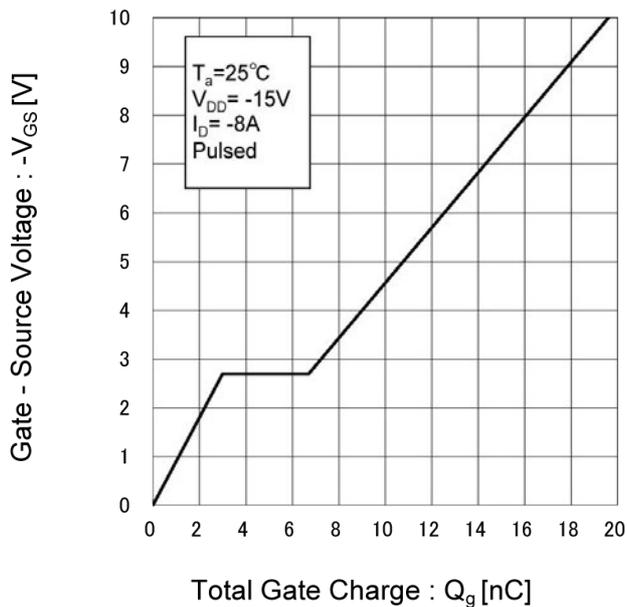
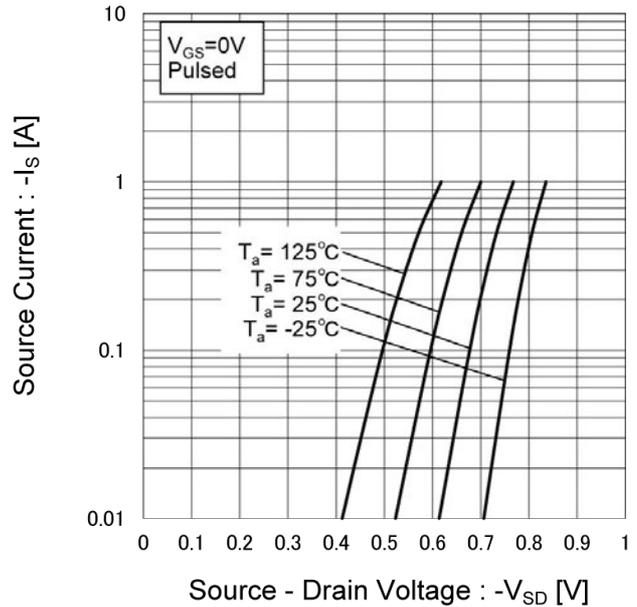


Fig.20 Source Current vs. Source Drain Voltage



● Measurement circuits <Tr1>

Fig.1-1 Switching Time Measurement Circuit

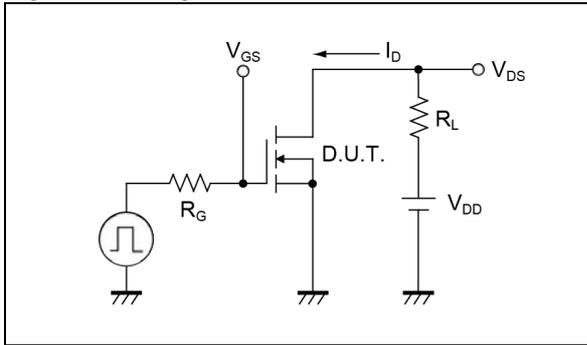


Fig.1-2 Switching Waveforms

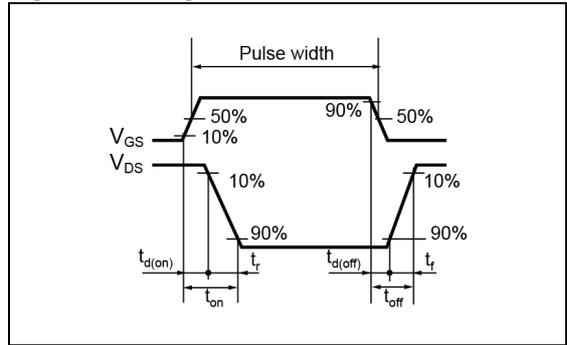


Fig.2-1 Gate Charge Measurement Circuit

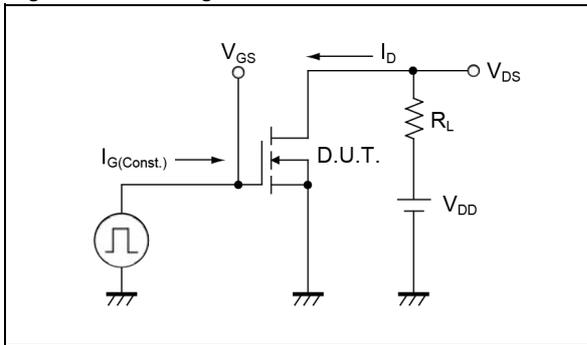


Fig.2-2 Gate Charge Waveform

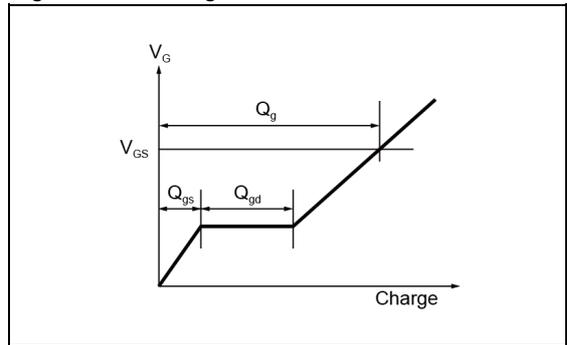


Fig.3-1 Avalanche Measurement Circuit

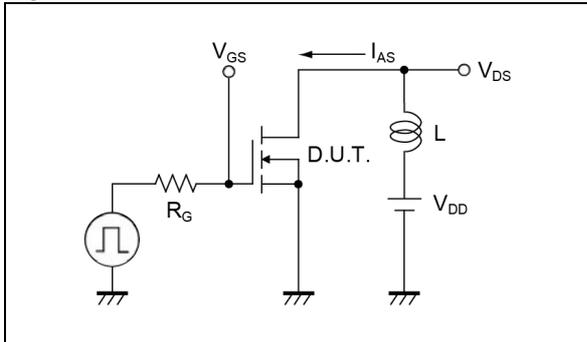
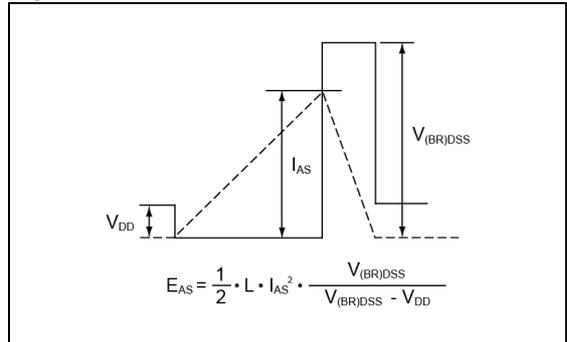


Fig.3-2 Avalanche Waveform



● Measurement circuits <Tr2>

Fig.4-1 Switching Time Measurement Circuit

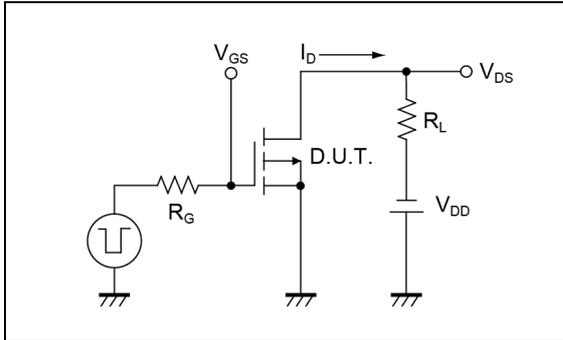


Fig.4-2 Switching Waveforms

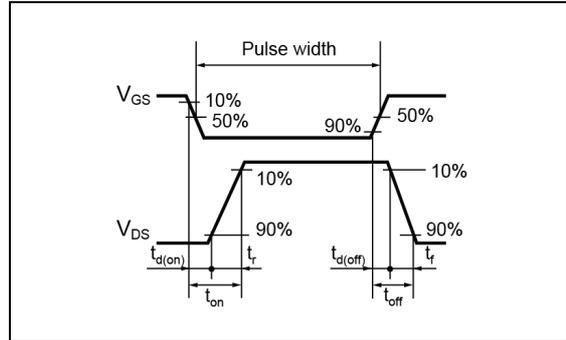


Fig.5-1 Gate Charge Measurement Circuit

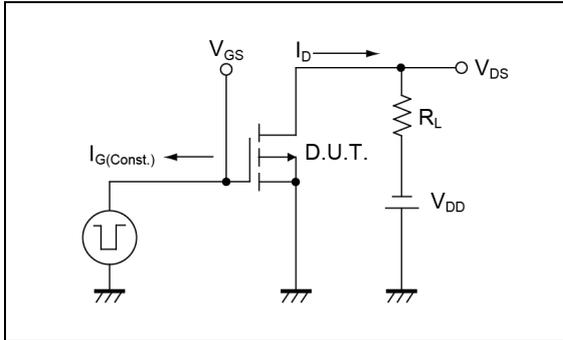


Fig.5-2 Gate Charge Waveform

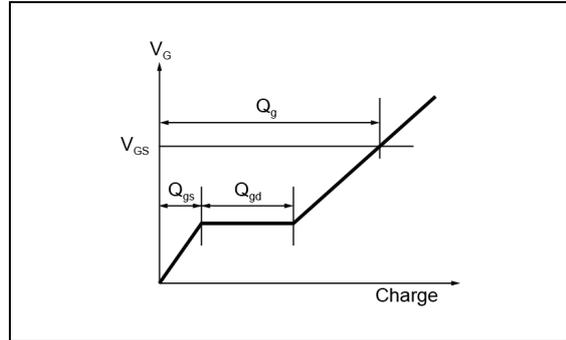


Fig.6-1 Avalanche Measurement Circuit

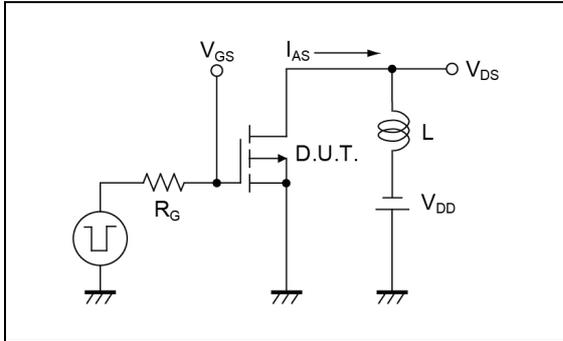
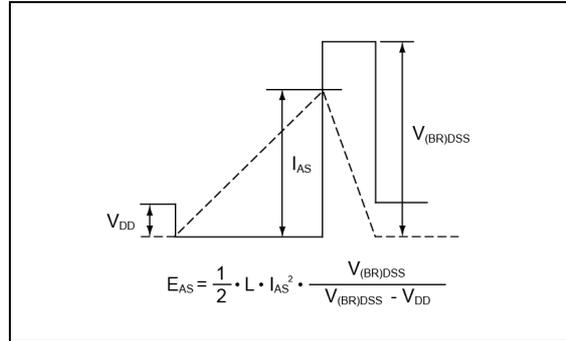


Fig.6-2 Avalanche Waveform

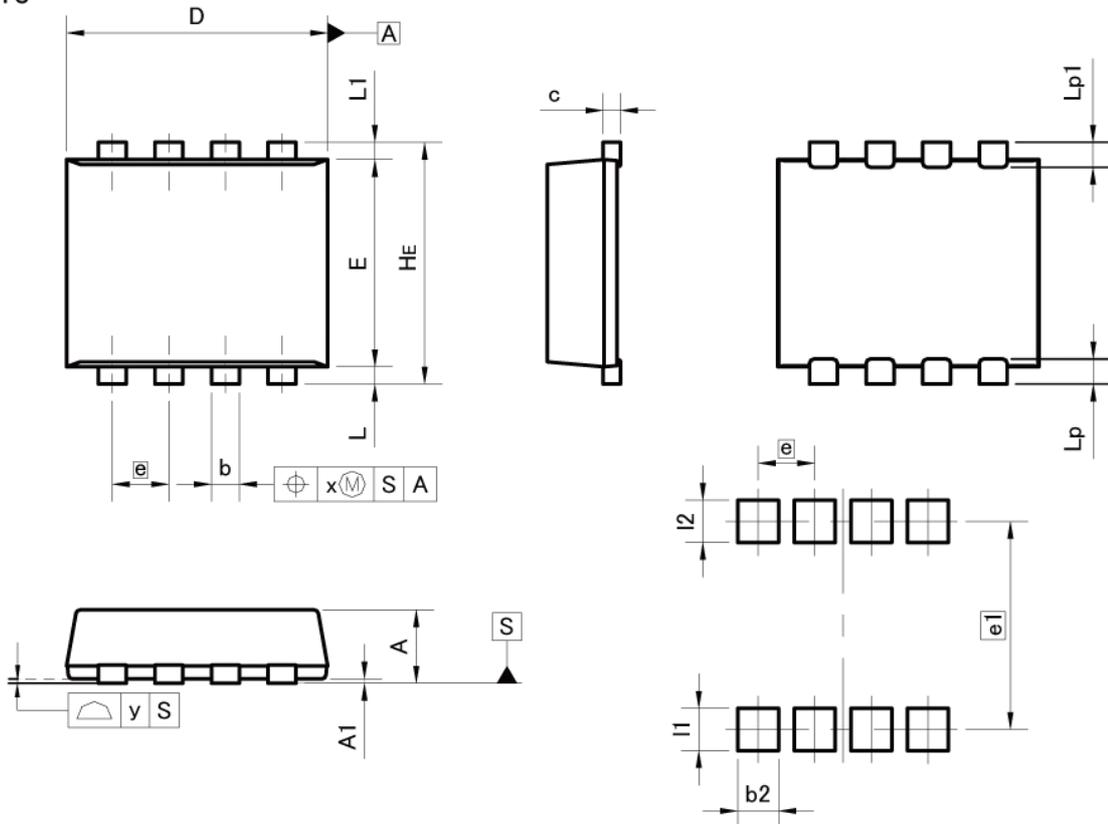


● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

●Dimensions

TSMT8



Pattern of terminal position areas  
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.47	-	0.019
e1	2.41		0.095	
l1	-	0.49	-	0.019
l2	-	0.49	-	0.019

Dimension in mm/inches

## Notes

- 1) The information contained herein is subject to change without notice.
- 2) Before you use our Products, please contact our sales representative and verify the latest specifications :
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.  
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Products beyond the rating specified by ROHM.
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- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
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- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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